

### **LISTING OF THE CLAIMS**

1 (currently amended): A semiconductor device, using a bonding material for linking a semiconductor terminal to a connecting terminal for an outside circuit, characterized by reinforcing the bonding material and/or a joint ~~bulb~~ between the semiconductor terminal and a the connecting material-terminal with a reinforcing material.

2 (original): A semiconductor device according to claim 1 characterized in that the bonding material is a bonding wire and/or a bump.

3 (original): A semiconductor device, using a bonding wire for linking a semiconductor terminal to a connecting terminal for an outside circuit, characterized by reinforcing the bonding wire, either partially or wholly, with a reinforcing material after bonding work.

Claims 4-9: (canceled).

10 (original): A semiconductor device according to claim 1 characterized in that the bonding material consists of any one of gold, tin, copper, aluminum and an alloy of any of these metals.

Claims 11-16: (canceled).

17 (currently amended): A semiconductor device, using a bonding wire for linking a semiconductor terminal to a connecting terminal for an outside circuit, characterized by: ~~the diameter of the bonding wire being~~ having a diameter of less than 20  $\mu\text{m}$ ; and reinforcing the bonding wire, either partially or wholly, with a reinforcing material after bonding work.

Claims 18-21: (canceled).

22 (previously presented): A semiconductor device according to claim 1 characterized in that the bonding material and the reinforcing material consist of different materials.

23 (previously presented): A semiconductor device according to claim 3 characterized in that the bonding material and the reinforcing material consist of different materials.

Claims 24-45: (canceled).

46 (new): A semiconductor device according to claim 1 characterized in that the reinforcing material is a metal coating and/or an inorganic material coating covering the bonding material or joint.

47 (new): A semiconductor device according to claim 3 characterized in that the reinforcing material is a metal coating and/or an inorganic material coating covering the bonding wire.

48 (new): A semiconductor device according to claim 46 characterized in that the metal coating is a metal comprising one or more of nickel, copper, gold, tin, solder, silver, cobalt, chromium, platinum, palladium and tungsten.

49 (new): A semiconductor device according to claim 47 characterized in that the metal coating is a metal comprising one or more of nickel, copper, gold, tin, solder, silver, cobalt, chromium, platinum, palladium and tungsten.

50 (new): A semiconductor device according to claim 49 characterized by forming a diffusion layer at an interface between the metal coating and the bonding wire.

51 (new): A semiconductor device according to claim 3 characterized in that the bonding wire is fabricated from any one of gold, copper, aluminum, silver and an alloy of any of these metals.

52 (new): A semiconductor device according to claim 51 wherein the bonding wire is gold or a gold alloy and an outermost surface of the bonding wire has a gold concentration of 99% or less.

53 (new): A semiconductor device according to claim 1 characterized by coating the semiconductor terminal, the connecting terminal and the bonding material and/or joint with resin.

54 (new): A semiconductor device according to claim 3 characterized by coating the semiconductor terminal, the connecting terminal and the bonding wire with resin.

55 (new): A semiconductor device according to claim 53 characterized in that the resin is a semiconductor sealing resin containing ceramic filler.

56 (new): A semiconductor device according to claim 54 characterized in that the resin is a semiconductor sealing resin containing ceramic filler.

57 (new): A semiconductor device according to claim 1 characterized by forming the connecting terminal using a substrate, a lead frame or a TAB tape.

58 (new): A semiconductor device according to claim 3 characterized by forming the connecting terminal using a substrate, a lead frame or a TAB tape.

59 (new): A semiconductor device according to claim 1 characterized by forming the semiconductor terminal on any one of a semiconductor chip, a substrate, a lead frame or a TAB tape.

60 (new): A semiconductor device according to claim 3 characterized by forming the semiconductor terminal on any one of a semiconductor chip, a substrate, a lead frame or a TAB tape.

61 (new): A semiconductor device according to claim 1 characterized in that the semiconductor terminal has a surface made of copper, aluminum, nickel, cobalt, gold, silver or an alloy of any of these metals.

62 (new): A semiconductor device according to claim 3 characterized in that the semiconductor terminal has a surface made of copper, aluminum, nickel, cobalt, gold, silver or an alloy or any of these metals.